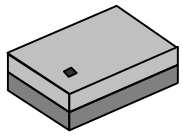
GNSS Front-End Module

■ GENERAL DESCRIPTION

The NJG1159PHH is a front-end module (FEM) designed for GNSS including GPS, GLONASS, BeiDou, and Galileo applications. This FEM offers low noise figure, high linearity, and high out-band rejection characteristics brought by included high performance pre-SAW filter and low noise amplifier (LNA). This FEM can operate from 1.5V to 3.3V single voltage in -40 to 105°C. This FEM has stand-by mode to save current consumption.

This FEM offers very small mounting area by included one SAW filter, only two external components, and very small package HFFP10-HH that is 1.5x1.1mm.

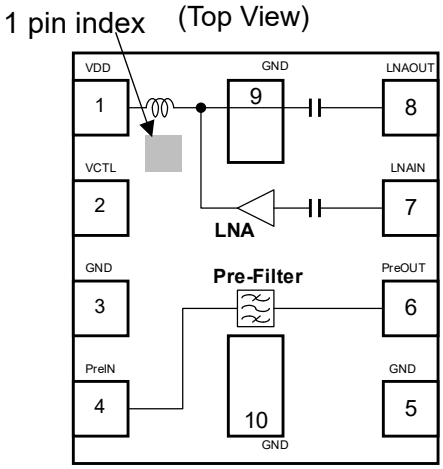
■ PACKAGE OUTLINE



■ FEATURES

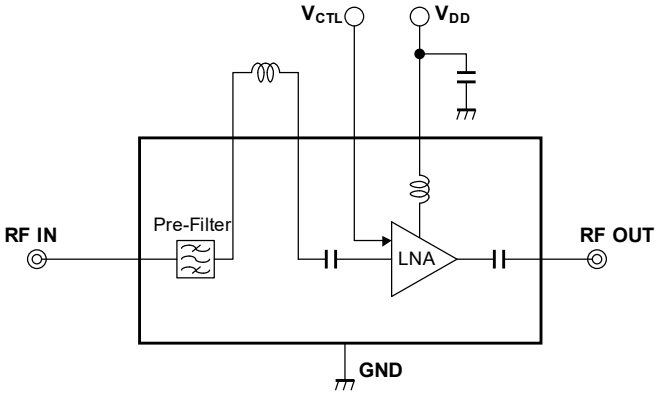
- Available for GNSS
- Low supply voltage — 1.8/ 2.8V typ.
- Low current consumption — 3.0/3.7mA typ. @V_{DD}=1.8/ 2.8V, V_{CTL}=1.8V
  0.1μA typ. @V_{DD}=1.8/ 2.8V, V_{CTL}=0V (Stand-by mode)
- High gain — 15.5/16.0dB typ. @V_{DD}=1.8/ 2.8V, V_{CTL}=1.8V, f=1575MHz, 1559 to 1591MHz
- Low noise figure — 1.55/1.50dB typ. @V_{DD}=1.8/ 2.8V, V_{CTL}=1.8V, f=1575MHz
  1.70/1.65dB typ. @V_{DD}=1.8/ 2.8V, V_{CTL}=1.8V, f=1597 to 1606MHz
  1.75/1.70dB typ. @V_{DD}=1.8/ 2.8V, V_{CTL}=1.8V, f=1559 to 1591MHz
- High out band rejection — 55dBc typ. @f=704 to 915MHz, relative to 1575MHz
  43dBc typ. @f=1710 to 1980MHz, relative to 1575MHz
  51dBc typ. @f=2400 to 2500MHz, relative to 1575MHz
- Small package size — HFFP10-HH: 1.5mmx1.1mm (typ.), t=0.5mm (max.)
- RoHS compliant and Halogen Free, MSL1

■ PIN CONFIGURATION



Pin Connection
1. VDD
2. VCTL
3. GND
4. PreIN
5. GND
6. PreOUT
7. LNAIN
8. LNAOUT
9. GND
10. GND

■ BLOCK DIAGRAM



■ TRUTH TABLE

"H"=V_{CTL}(H), "L"=V_{CTL}(L)

VCTL	Mode
H	Active mode
L	Stand-by mode

Note: Specifications and description listed in this datasheet are subject to change without notice.

■ ABSOLUTE MAXIMUM RATINGS

T_a=+25°C, Z_s=Z_l=50Ω

PARAMETERS	SYMBOL	CONDITIONS	RATINGS	UNITS
Supply voltage	V_{DD}		5.0	V
Control voltage	V_{CTL}		5.0	V
Input power	P_{IN} (inband)	V_{DD}=2.8V, f=1575, 1597 to 1606, 1559 to 1591MHz	10	dBm
	P_{IN} (outband)	V_{DD}=2.8V, f=50 to 1460, 1710 to 4000MHz	25	dBm
Power dissipation	P_D	4-layer FR4 PCB without through-hole (101.5x114.5mm), T_j=110°C	560	mW
Operating temperature	T_{opr}		-40 to +105	°C
Storage temperature	T_{stg}		-40 to +110	°C

■ ELECTRICAL CHARACTERISTICS 1 (DC)

(General conditions: T_a=+25°C)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Supply Voltage	V_{DD}		1.5	-	3.3	V
Control Voltage (High)	$V_{CTL(H)}$		1.5	1.8	3.3	V
Control Voltage (Low)	$V_{CTL(L)}$		0	0	0.3	V
Supply Current 1	I_{DD1}	RF OFF, V_{DD}=2.8V, V_{CTL}=1.8V	-	3.7	-	mA
Supply Current 2	I_{DD2}	RF OFF, V_{DD}=1.8V, V_{CTL}=1.8V	-	3.0	-	mA
Supply Current 3	I_{DD3}	RF OFF, V_{DD}=2.8V, V_{CTL}=0V	-	0.1	5.0	μA
Supply Current 4	I_{DD4}	RF OFF, V_{DD}=1.8V, V_{CTL}=0V	-	0.1	5.0	μA
Control Current	I_{CTL}	V_{CTL}=1.8V	-	5.0	15.0	μA

■ ELECTRICAL CHARACTERISTICS 2 (RF)

General conditions: V_{DD}=2.8V, V_{CTL}=1.8V, f_{RF}=1575MHz, 1597 to 1606, 1559 to 1591MHz, T_a=+25°C, Z_s=Z_l=50Ω, with application circuit

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Small Signal Gain (GPS)1	GainGPS1	f=1575MHz (GPS) Exclude PCB, Connector Losses (0.17dB)	-	16.0	-	dB
Small Signal Gain (GLONASS)1	GainGLN1	f=1597 to 1606MHz (GLONASS) Exclude PCB, Connector Losses (0.17dB)	-	16.5	-	dB
Small Signal Gain (BeiDou, Galileo)1	GainBG1	f=1559 to 1591MHz (BeiDou, Galileo) Exclude PCB, Connector Losses (0.17dB)	-	16.0	-	dB
Noise Figure (GPS)1	NFGPS1	f=1575MHz (GPS)Exclude PCB, Connector Losses (0.09dB)	-	1.50	-	dB
Noise Figure (GLONASS)1	NFGLN1	f=1597 to 1606MHz (GLONASS) Exclude PCB, Connector Losses (0.09dB)	-	1.65	-	dB
Noise Figure (BeiDou, Galileo)1	NFBG1	f=1559 to 1591MHz (BeiDou, Galileo) Exclude PCB, Connector Losses (0.09dB)	-	1.70	-	dB
Input Power at 1dB Gain Compression Point 1	P-1dB(IN)1	f=1575, 1597 to 1606, 1559 to 1591MHz	-	-10.0	-	dBm
Input 3rd Order Intercept Point 1	IIP3_1	f1=1575,1597 to 1606,1559 to 1591MHz, f2=f1 +/-1MHz, Pin=-30dBm	-	-2.0	-	dBm
Out of Band Input 2nd Order Intercept Point 1	IIP2_OB1	f1=824.6MHz at +15dBm, f2=2400MHz at +15dBm, fmeas=1575.4MHz	-	+80	-	dBm
Out of Band Input 3rd Order Intercept Point 1	IIP3_OB1	f1=1712.7MHz at +15dBm, f2=1850MHz at +15dBm, fmeas=1575.4MHz	-	+55	-	dBm
700MHz Harmonic1	2fo1	Input jammer tone: 787.76MHz at +15dBm Measure the harmonic tone at 1575.52MHz	-	-37	-	dBm
Out-of-Band Input Power 1dB Compression 1	P-1dB(IN) _OB1-1	fjam=900MHz, fmeas=1575MHz at Pin=-40dBm	-	+24	-	dBm
	P-1dB(IN) _OB1-2	fjam=1710MHz, fmeas=1575MHz at Pin=-40dBm	-	+24	-	dBm
Low Band Rejection 1	BR_L1	f=704 to 915MHz, relative to 1575MHz	-	55	-	dBc
High Band Rejection 1	BR_H1	f=1710 to 1980MHz, relative to 1575MHz	-	43	-	dBc
WLAN Band Rejection 1	BR_W1	f=2400 to 2500MHz, relative to 1575MHz	-	51	-	dBc
RF IN Return Loss (GPS)1	RLiGPS1	f=1575MHz (GPS)	-	10	-	dB
RF IN Return Loss (GLONASS)1	RLiGLN1	f=1597 to 1606MHz (GLONASS)	-	15	-	dB
RF IN Return Loss (BeiDou, Galileo)1	RLiBG1	f=1559 to 1591MHz (BeiDou, Galileo)	-	13	-	dB
RF OUT Return Loss (GPS)1	RLoGPS1	f=1575MHz (GPS)	-	15	-	dB
RF OUT Return Loss (GLONASS)1	RLoGLN1	f=1597 to 1606MHz (GLONASS)	-	15	-	dB
RF OUT Return Loss (BeiDou, Galileo)1	RLoBG1	f=1559 to 1591MHz (BeiDou, Galileo)	-	15	-	dB
Group Delay Time Deviation (GLONASS) 1	GDTDGLN1	f=1597 to 1606MHz (GLONASS)	-	3	-	ns
Group Delay Time Deviation (BeiDou)1	GDTDB1	f=1559 to 1563.2MHz (BeiDou)	-	4	-	ns
Group Delay Time Deviation (Galileo)1	GDTDG1	f=1559 to 1591MHz (Galileo)	-	9	-	ns

■ ELECTRICAL CHARACTERISTICS 3 (RF)

General conditions: V_{DD}=1.8V, V_{CTL}=1.8V, f_{RF}=1575MHz, 1597 to 1606, 1559 to 1591MHz, T_a=+25°C, Z_s=Z_l=50Ω, with application circuit

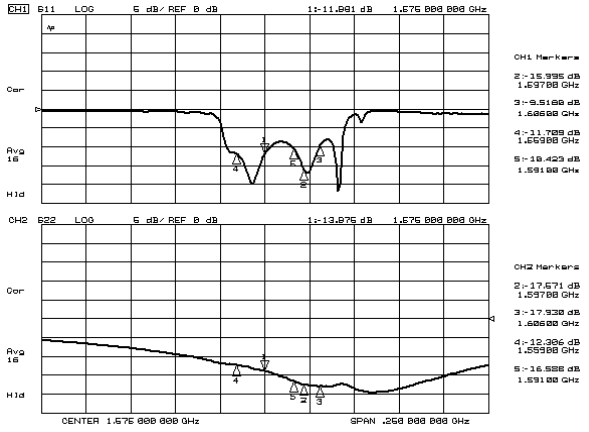
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Small Signal Gain (GPS)2	GainGPS2	f=1575MHz (GPS) Exclude PCB, Connector Losses (0.17dB)	-	15.5	-	dB
Small Signal Gain (GLONASS)2	GainGLN2	f=1597 to 1606MHz (GLONASS) Exclude PCB, Connector Losses (0.17dB)	-	16.0	-	dB
Small Signal Gain (BeiDou, Galileo)2	GainBG2	f=1559 to 1591MHz (BeiDou, Galileo) Exclude PCB, Connector Losses (0.17dB)	-	15.5	-	dB
Noise Figure (GPS)2	NFGPS2	f=1575MHz (GPS)Exclude PCB, Connector Losses (0.09dB)	-	1.55	-	dB
Noise Figure (GLONASS)2	NFGLN2	f=1597 to 1606MHz (GLONASS) Exclude PCB, Connector Losses (0.09dB)	-	1.70	-	dB
Noise Figure (BeiDou, Galileo)2	NFBG2	f=1559 to 1591MHz (BeiDou, Galileo) Exclude PCB, Connector Losses (0.09dB)	-	1.75	-	dB
Input Power at 1dB Gain Compression Point 2	P-1dB(IN)2	f=1575, 1597 to 1606, 1559 to 1591MHz	-	-13.0	-	dBm
Input 3rd Order Intercept Point 2	IIP3_2	f1=1575, 1597 to 1606, 1559 to 1591MHz, f2=f1 +/-1MHz, Pin=-30dBm	-	-5.0	-	dBm
Out of Band Input 2nd Order Intercept Point 2	IIP2_OB2	f1=824.6MHz at +15dBm, f2=2400MHz at +15dBm, fmeas=1575.4MHz	-	+80	-	dBm
Out of Band Input 3rd Order Intercept Point 2	IIP3_OB2	f1=1712.7MHz at +15dBm, f2=1850MHz at +15dBm, fmeas=1575.4MHz	-	+55	-	dBm
700MHz Harmonic2	2fo2	Input jammer tone: 787.76MHz at +15dBm Measure the harmonic tone at 1575.52MHz	-	-37	-	dBm
Out-of-Band Input Power 1dB Compression 2	P-1dB(IN)_OB2-1	fjam=900MHz, fmeas=1575MHz at Pin=-40dBm	-	+24	-	dBm
	P-1dB(IN)_OB2-2	fjam=1710MHz, fmeas=1575MHz at Pin=-40dBm	-	+24	-	dBm
Low Band Rejection 2	BR_L2	f=704 to 915MHz, relative to 1575MHz	-	55	-	dBc
High Band Rejection 2	BR_H2	f=1710 to 1980MHz, relative to 1575MHz	-	43	-	dBc
WLAN Band Rejection 2	BR_W2	f=2400 to 2500MHz, relative to 1575MHz	-	51	-	dBc
RF IN Return Loss (GPS)2	RLiGPS2	f=1575MHz (GPS)	-	10	-	dB
RF IN Return Loss (GLONASS)2	RLiGLN2	f=1597 to 1606MHz (GLONASS)	-	15	-	dB
RF IN Return Loss (BeiDou, Galileo)2	RLiBG2	f=1559 to 1591MHz (BeiDou, Galileo)	-	13	-	dB
RF OUT Return Loss (GPS)2	RLoGPS2	f=1575MHz (GPS)	-	15	-	dB
RF OUT Return Loss (GLONASS)2	RLoGLN2	f=1597 to 1606MHz (GLONASS)	-	15	-	dB
RF OUT Return Loss (BeiDou, Galileo)2	RLoBG2	f=1559 to 1591MHz (BeiDou, Galileo)	-	15	-	dB
Group Delay Time Deviation (GLONASS) 2	GDTDGLN2	f=1597 to 1606MHz (GLONASS)	-	3	-	ns
Group Delay Time Deviation (BeiDou)2	GDTDB2	f=1559 to 1563.2MHz (BeiDou)	-	4	-	ns
Group Delay Time Deviation (Galileo)2	GDTDG2	f=1559 to 1591MHz (Galileo)	-	9	-	ns

■ **TERMINAL INFORMATION**

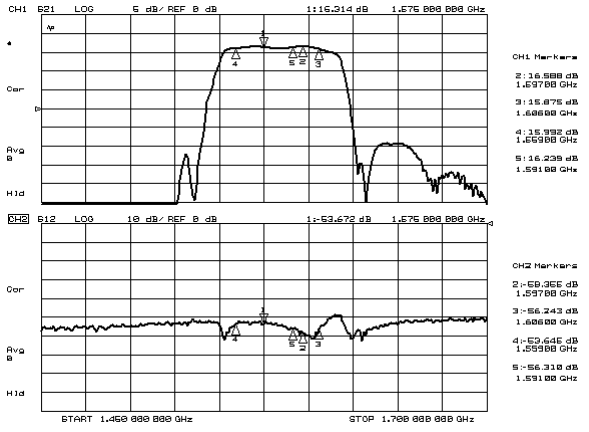
No.	SYMBOL	DESCRIPTION
1	VDD	Supply voltage terminal. Please connect bypass capacitor C1 with ground as close as possible.
2	VCTL	Control voltage terminal.
3	GND	Ground terminal. This terminal should be connected to the ground plane as close as possible for excellent RF performance.
4	PreIN	RF input terminal. This terminal connects to input of pre-SAW filter.
5	GND	Ground terminal. This terminal should be connected to the ground plane as close as possible for excellent RF performance.
6	PreOUT	Pre-SAW filter output terminal. This terminal connects to LNAIN with L1.
7	LNAIN	RF input terminal. This terminal requires only a matching inductor L1, and does not require DC blocking capacitor because of integrated capacitor.
8	LNAOUT	RF output terminal. This terminal requires no DC blocking capacitor since this terminal has integrated DC blocking capacitor.
9	GND	Ground terminal. This terminal should be connected to the ground plane as close as possible for excellent RF performance.
10	GND	Ground terminal. This terminal should be connected to the ground plane as close as possible for excellent RF performance.

■ ELECTRICAL CHARACTERISTICS

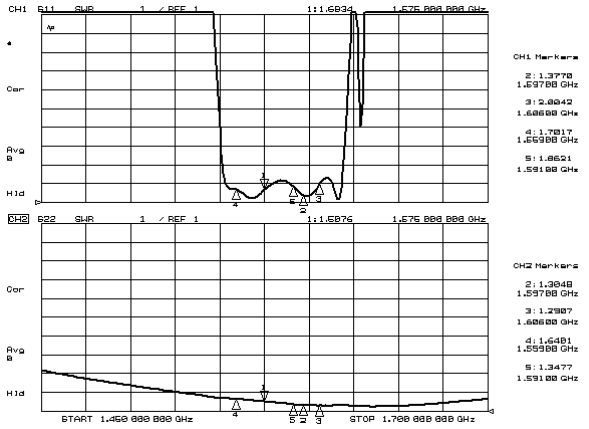
Conditions: V_{DD}=2.8V, V_{CTL}=1.8V, Ta=25°C, Z_s=Z_l=50Ω, with application circuit



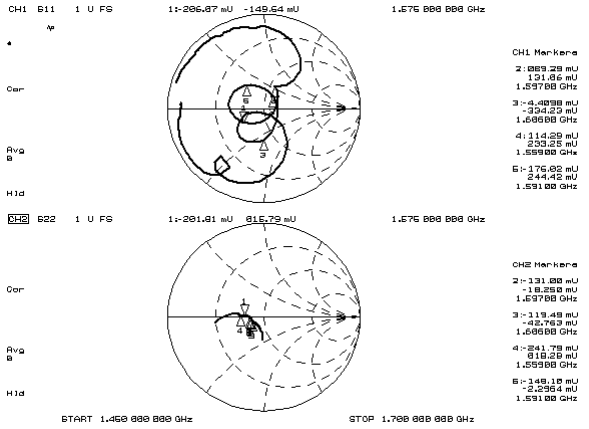
S11, S22



S21, S12



VSWR



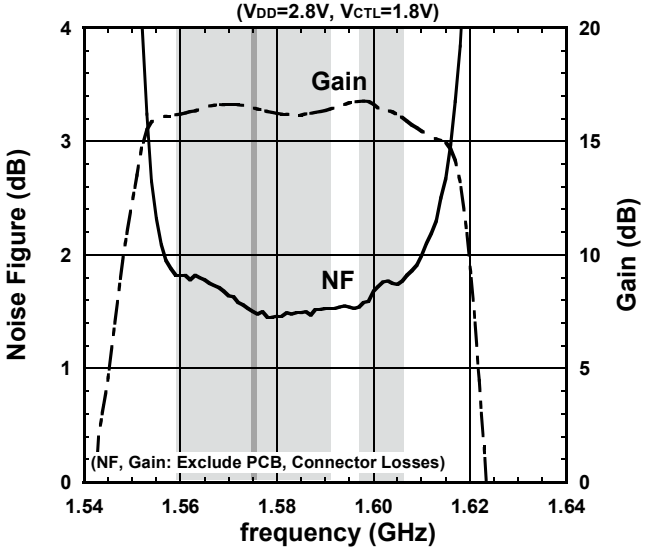
Zin, Zout

■ ELECTRICAL CHARACTERISTICS

Conditions: V_{DD}=2.8V, V_{CTL}=1.8V, Ta=25°C, Z_s=Z_l=50Ω, with application circuit

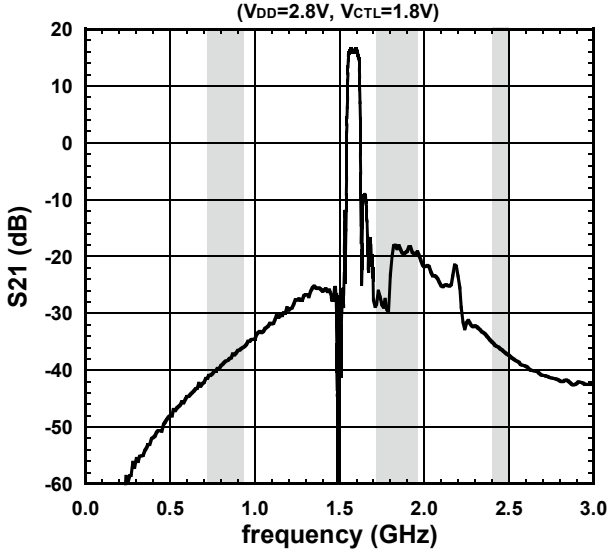
NF, Gain vs. frequency

(V_{DD}=2.8V, V_{CTL}=1.8V)



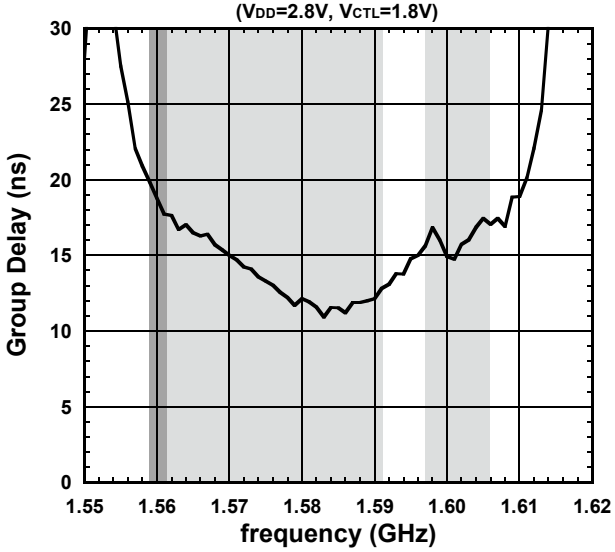
S21 vs. frequency

(V_{DD}=2.8V, V_{CTL}=1.8V)



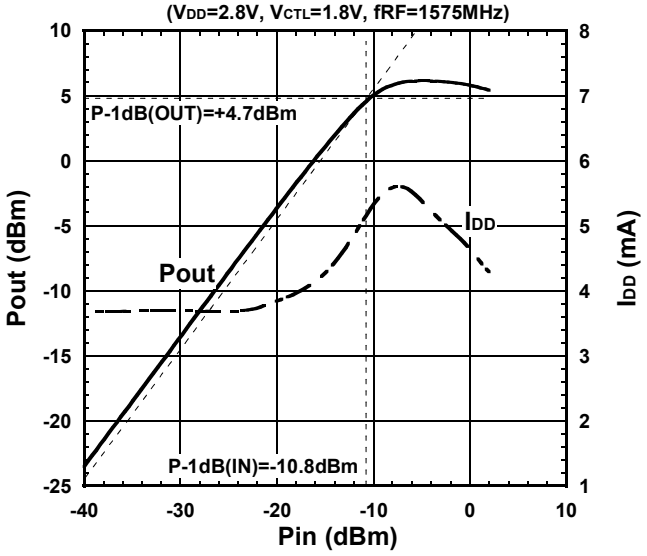
Group Delay vs. frequency

(V_{DD}=2.8V, V_{CTL}=1.8V)



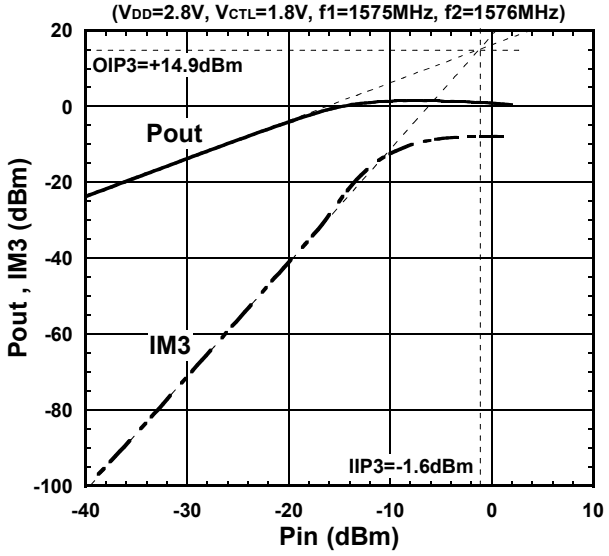
Pout, I_{DD} vs. Pin

(V_{DD}=2.8V, V_{CTL}=1.8V, fRF=1575MHz)



Pout, IM3 vs. Pin

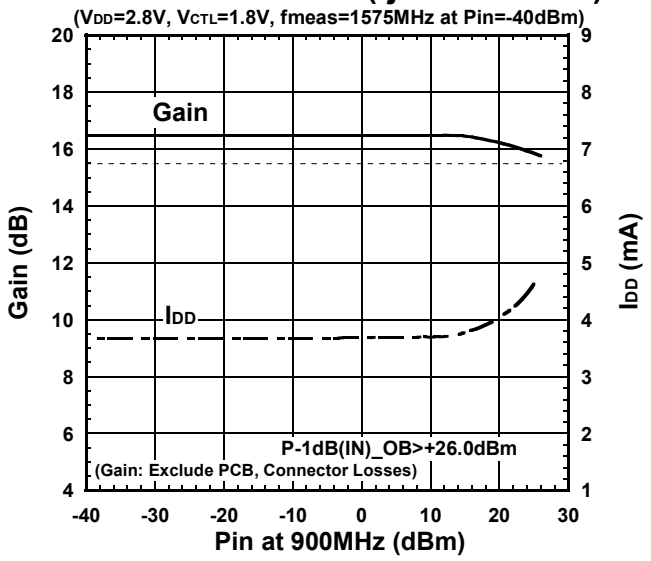
(V_{DD}=2.8V, V_{CTL}=1.8V, f1=1575MHz, f2=1576MHz)



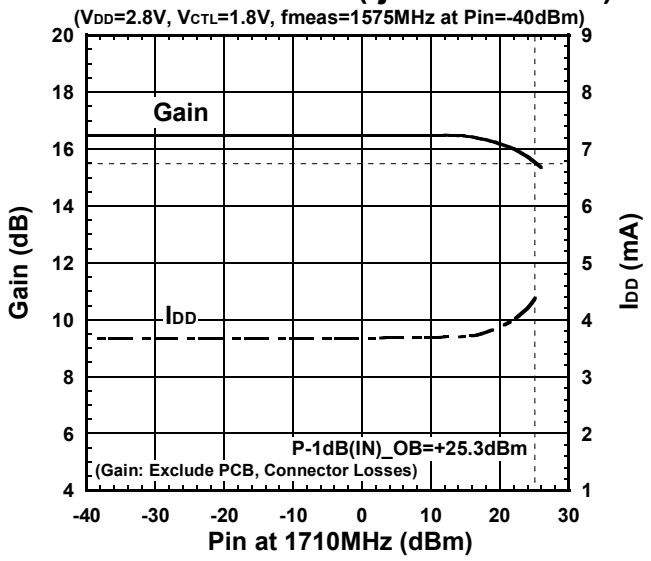
■ ELECTRICAL CHARACTERISTICS

Conditions: V_{DD}=2.8V, V_{CTL}=1.8V, Ta=25°C, Z_s=Z_l=50Ω, with application circuit

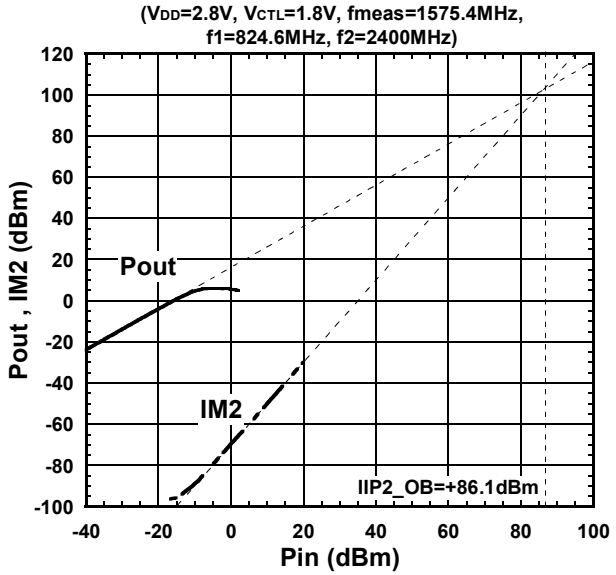
Out-of-band P-1dB (fjam=900MHz)



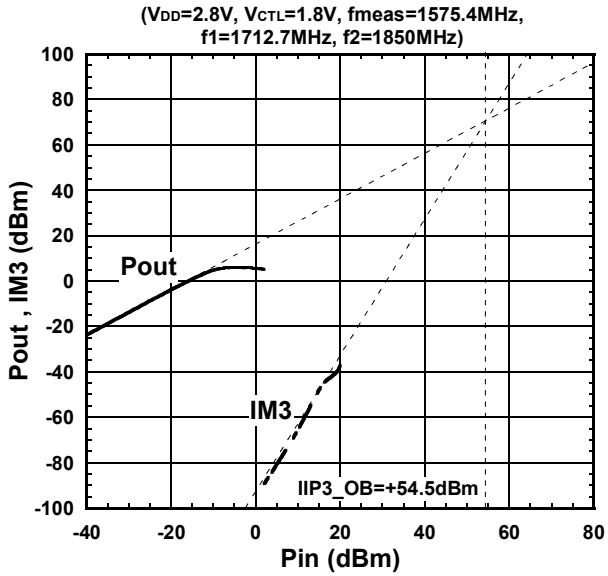
Out-of-band P-1dB (fjam=1710MHz)



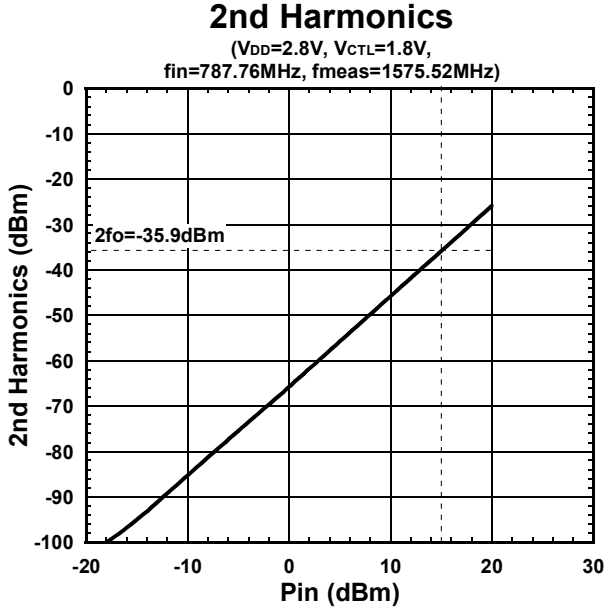
Out-of-band IIP2



Out-of-band IIP3

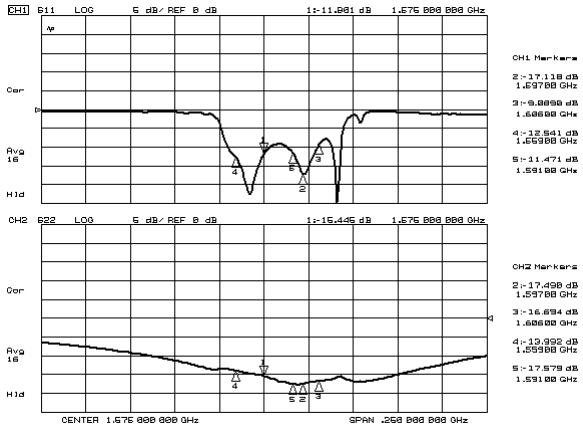


2nd Harmonics

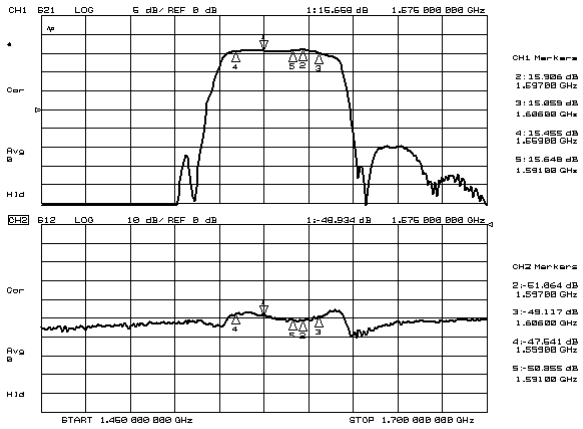


■ ELECTRICAL CHARACTERISTICS

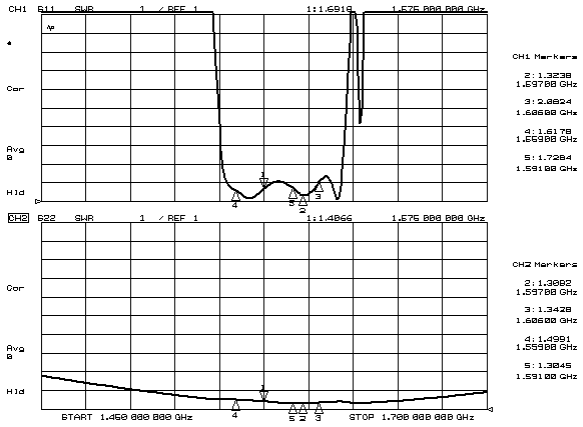
Conditions: V_{DD}=1.8V, V_{CTL}=1.8V, Ta=25°C, Z_s=Z_l=50Ω, with application circuit



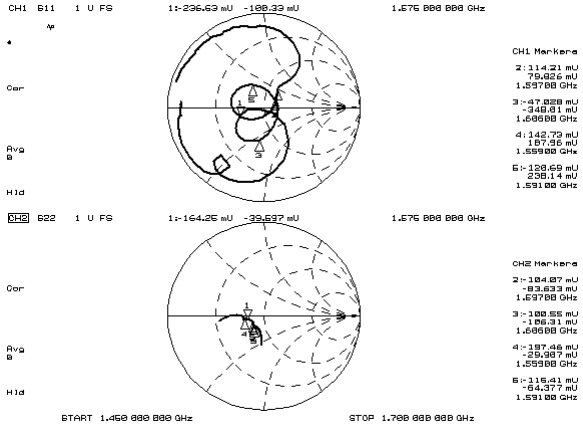
S11, S22



S21, S12



VSWR



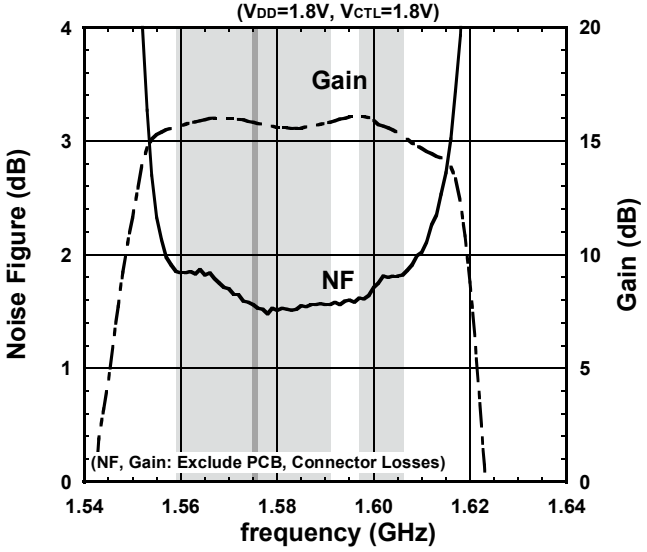
Zin, Zout

■ ELECTRICAL CHARACTERISTICS

Conditions: V_{DD}=1.8V, V_{CTL}=1.8V, Ta=25°C, Z_s=Z_l=50Ω, with application circuit

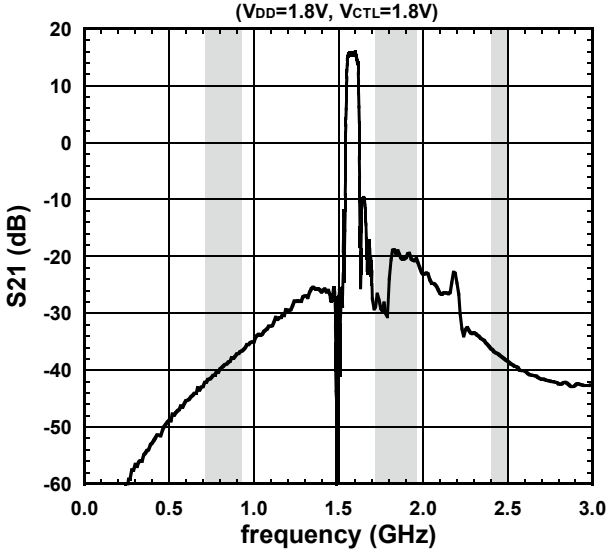
NF, Gain vs. frequency

(V_{DD}=1.8V, V_{CTL}=1.8V)



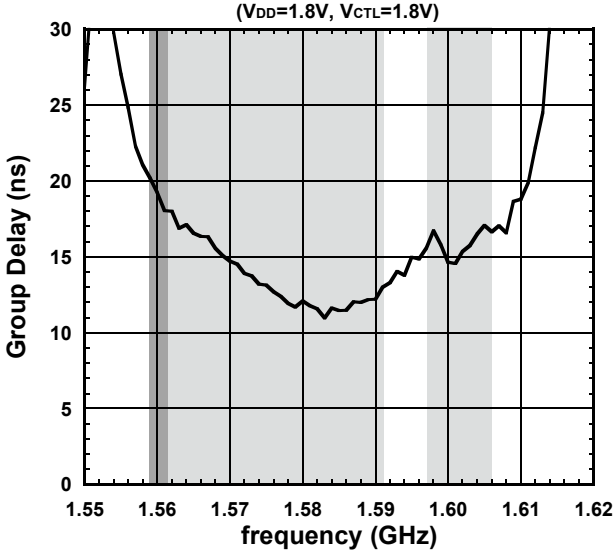
S21 vs. frequency

(V_{DD}=1.8V, V_{CTL}=1.8V)



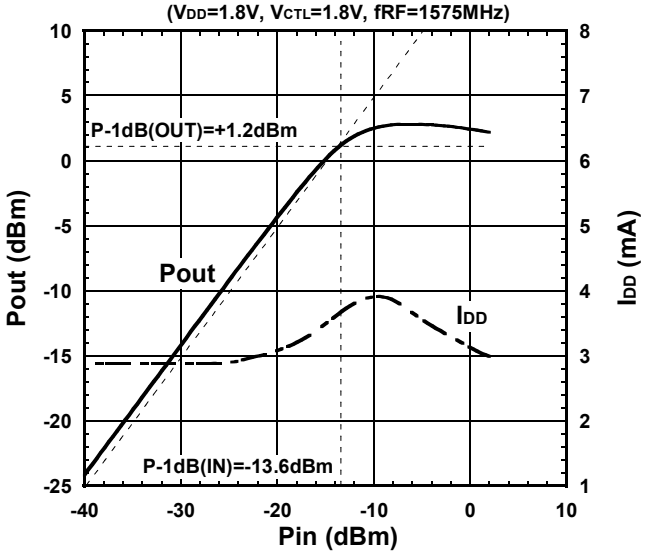
Group Delay vs. frequency

(V_{DD}=1.8V, V_{CTL}=1.8V)



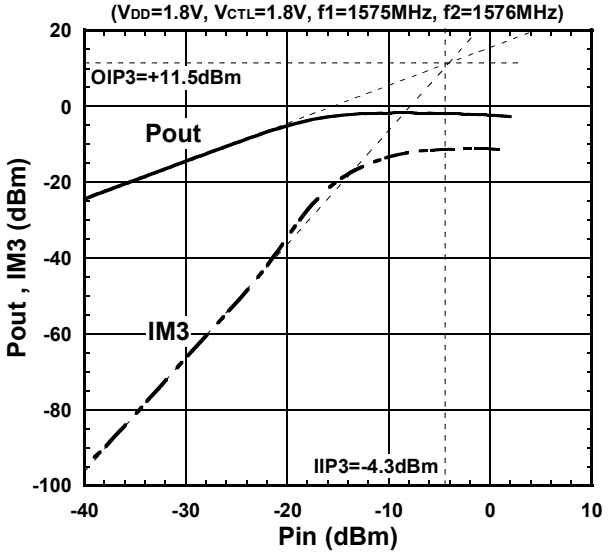
Pout, I_{DD} vs. Pin

(V_{DD}=1.8V, V_{CTL}=1.8V, fRF=1575MHz)



Pout, IM3 vs. Pin

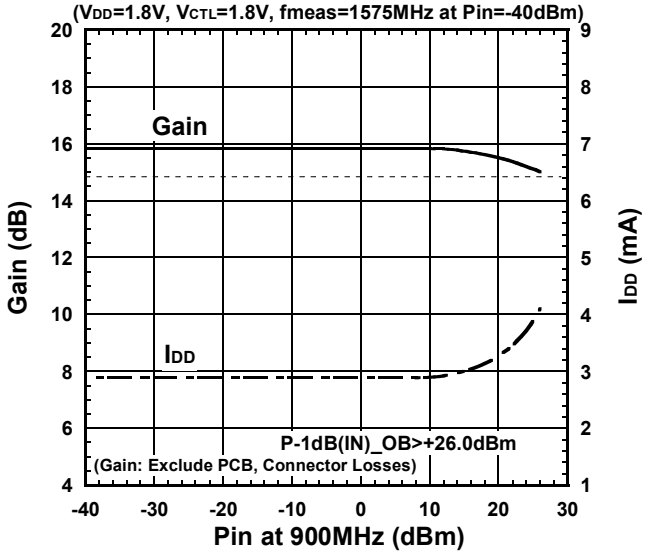
(V_{DD}=1.8V, V_{CTL}=1.8V, f1=1575MHz, f2=1576MHz)



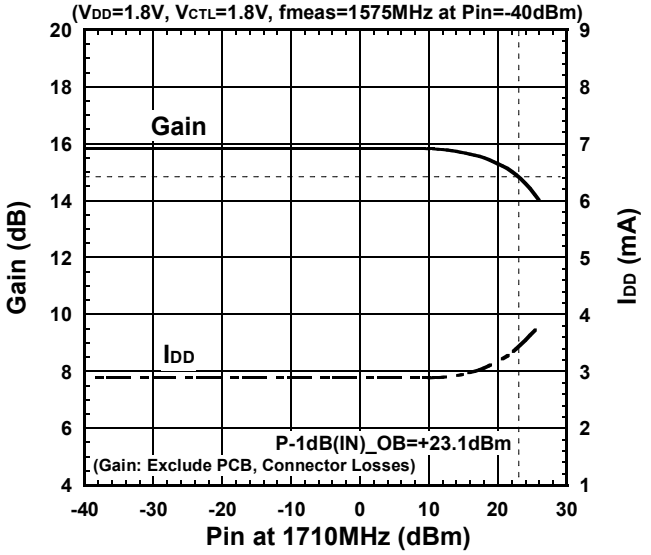
■ ELECTRICAL CHARACTERISTICS

Conditions: V_{DD}=1.8V, V_{CTL}=1.8V, Ta=25°C, Z_s=Z_l=50Ω, with application circuit

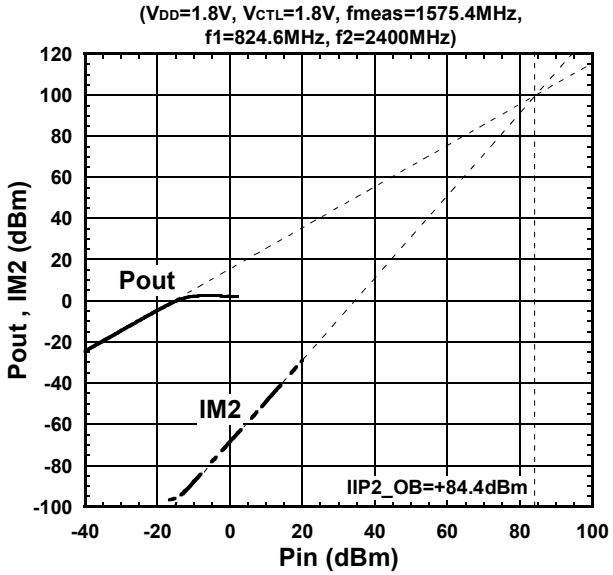
Out-of-band P-1dB (fjam=900MHz)



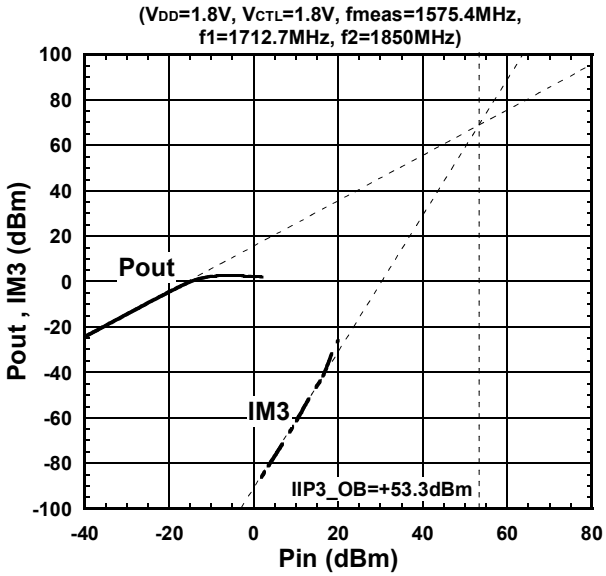
Out-of-band P-1dB (fjam=1710MHz)



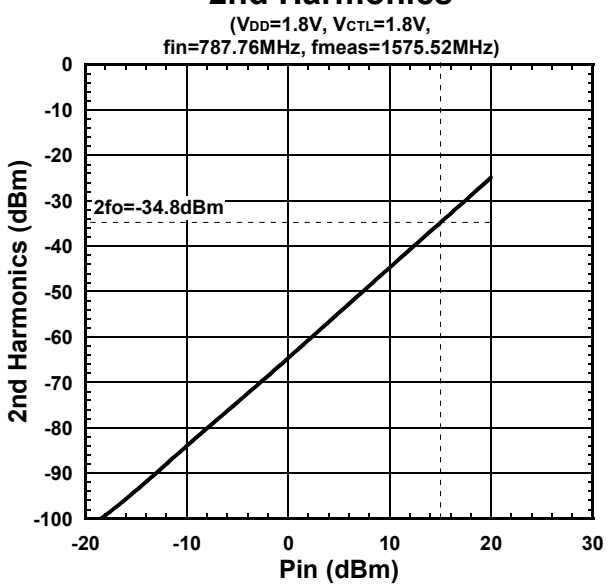
Out-of-band IIP2



Out-of-band IIP3



2nd Harmonics

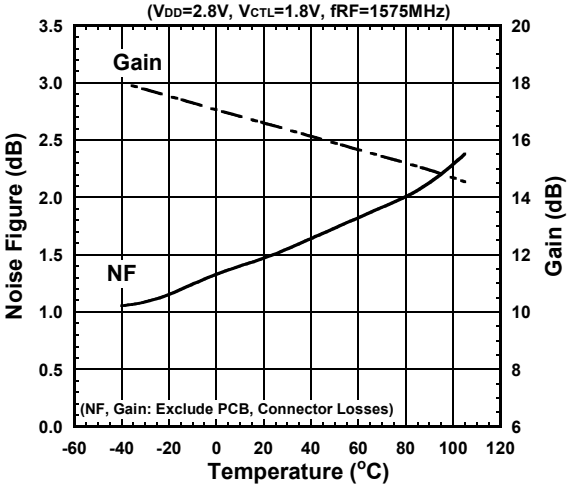


■ ELECTRICAL CHARACTERISTICS

Conditions: V_{DD}=2.8V, V_{CTL}=1.8V, Z_s=Z_l=50Ω, with application circuit

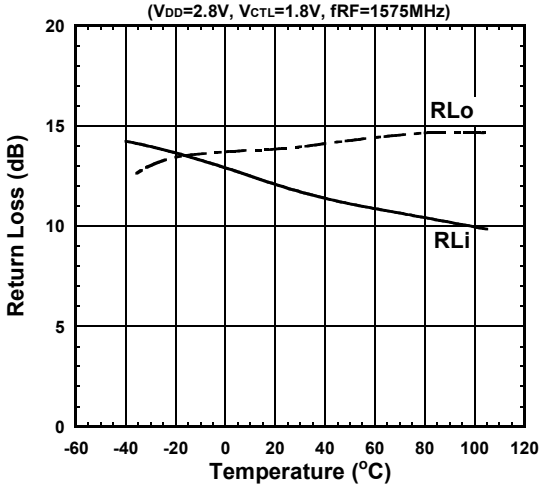
NF, Gain vs. Temperature

(V_{DD}=2.8V, V_{CTL}=1.8V, fRF=1575MHz)



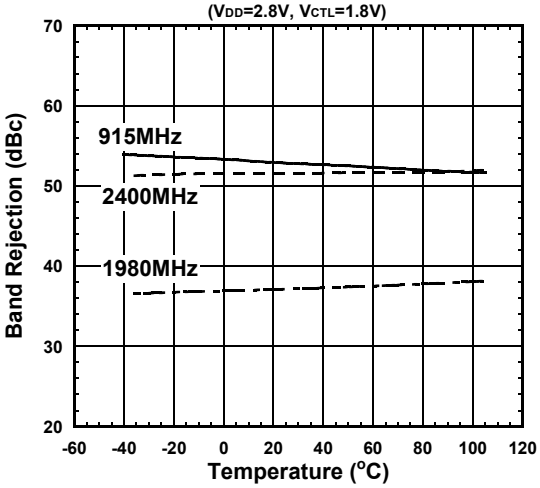
Return Loss vs. Temperature

(V_{DD}=2.8V, V_{CTL}=1.8V, fRF=1575MHz)



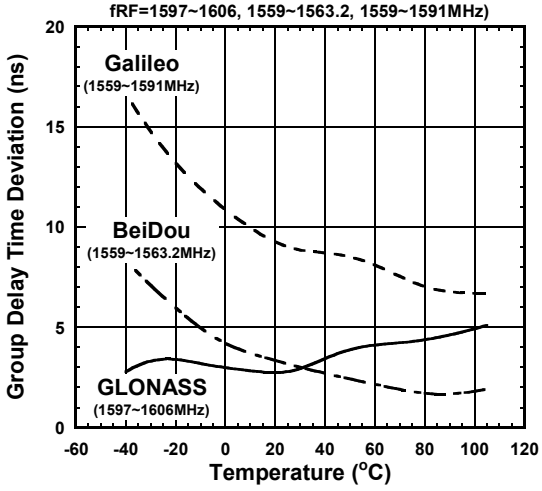
Band Rejection vs. Temperature

(V_{DD}=2.8V, V_{CTL}=1.8V)



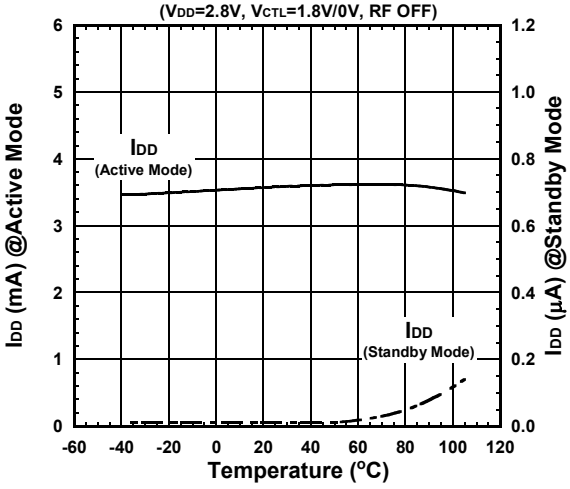
Group Delay Time Deviation vs. Temperature

(V_{DD}=2.8V, V_{CTL}=1.8V, fRF=1597~1606, 1559~1563.2, 1559~1591MHz)



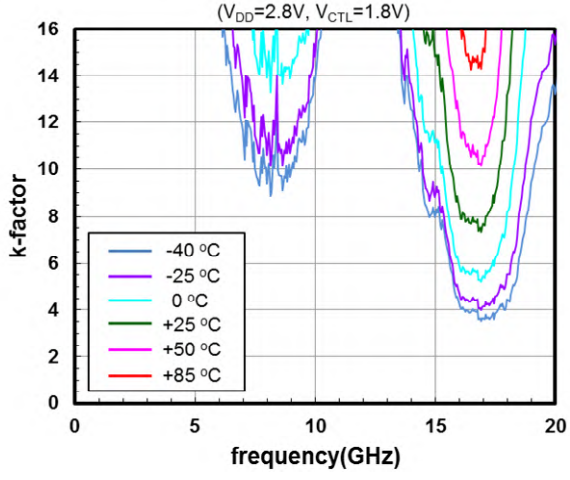
I_{DD} vs. Temperature

(V_{DD}=2.8V, V_{CTL}=1.8V/0V, RF OFF)



k-factor vs. frequency

(V_{DD}=2.8V, V_{CTL}=1.8V)

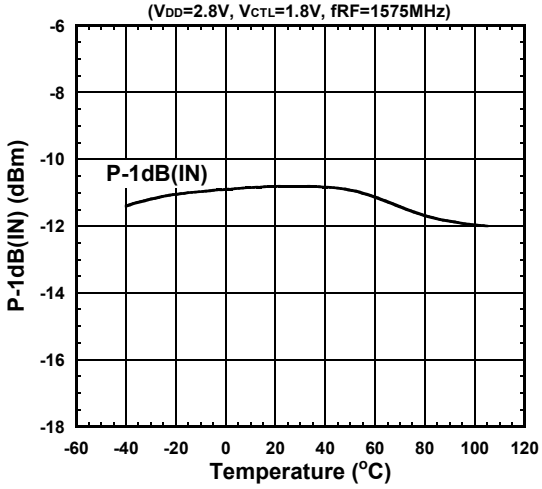


■ ELECTRICAL CHARACTERISTICS

Conditions: V_{DD}=2.8V, V_{CTL}=1.8V, Z_s=Z_l=50Ω, with application circuit

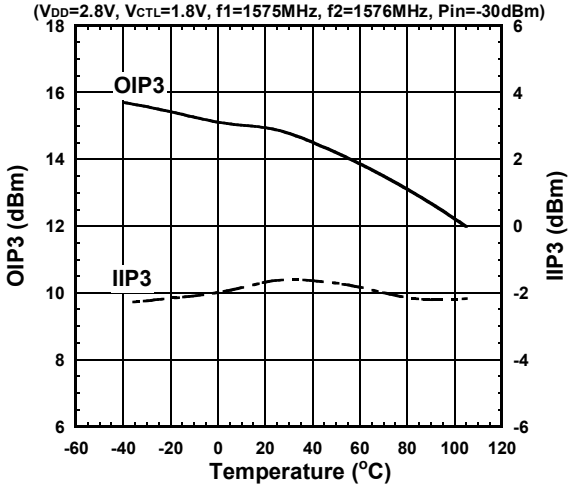
P-1dB(IN) vs. Temperature

(V_{DD}=2.8V, V_{CTL}=1.8V, fRF=1575MHz)



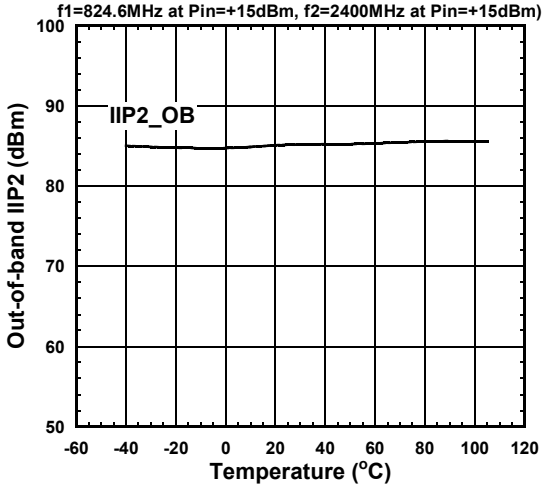
OIP3, IIP3 vs. Temperature

(V_{DD}=2.8V, V_{CTL}=1.8V, f1=1575MHz, f2=1576MHz, Pin=-30dBm)



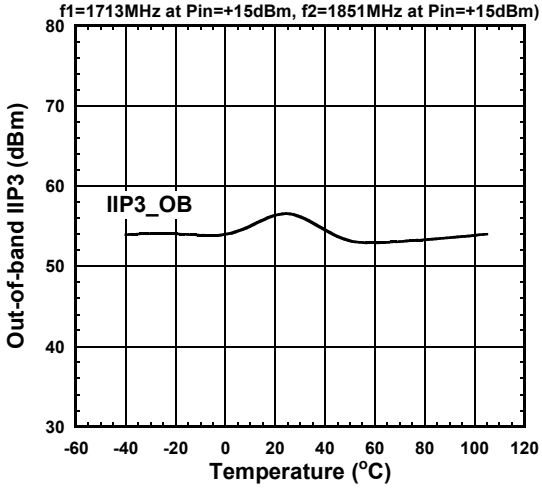
Out-of-band IIP2 vs. Temperature

(V_{DD}=2.8V, V_{CTL}=1.8V, fmeas=1575.4MHz, f1=824.6MHz at Pin=+15dBm, f2=2400MHz at Pin=+15dBm)



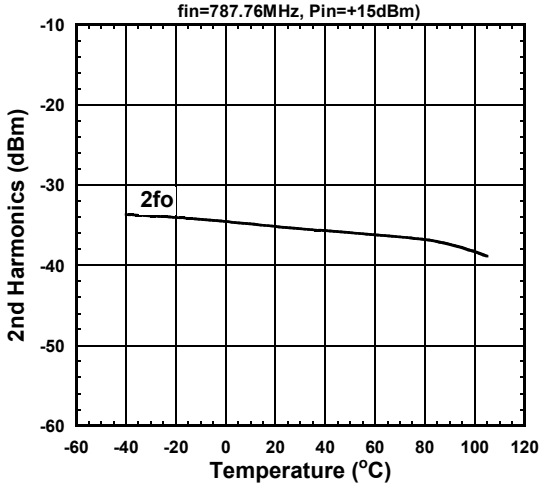
Out-of-band IIP3 vs. Temperature

(V_{DD}=2.8V, V_{CTL}=1.8V, fmeas=1575MHz, f1=1713MHz at Pin=+15dBm, f2=1851MHz at Pin=+15dBm)



2nd Harmonics vs. Temperature

(V_{DD}=2.8V, V_{CTL}=1.8V, fmeas=1575.52MHz, fin=787.76MHz, Pin=+15dBm)

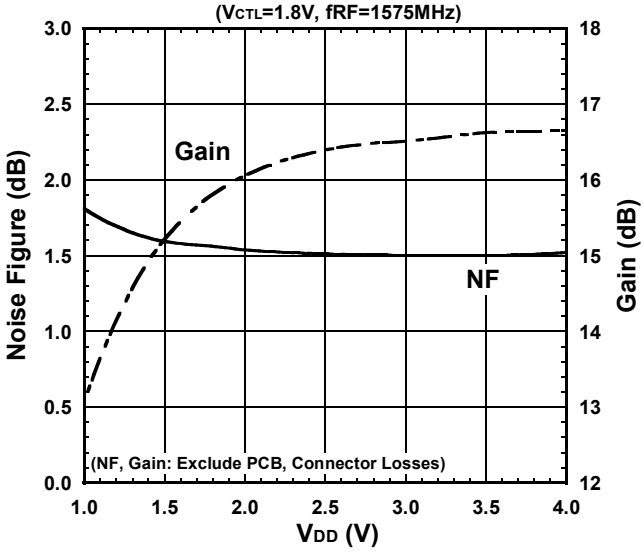


■ ELECTRICAL CHARACTERISTICS

Conditions: V_{CTL}=1.8V, Ta=25°C, Z_s=Z_l=50Ω, with application circuit

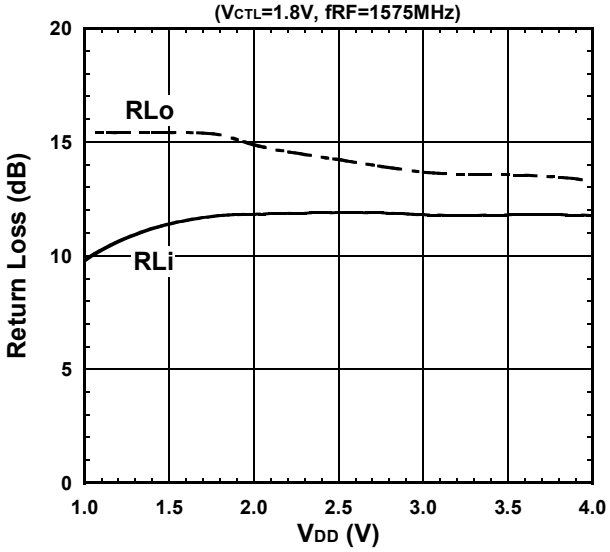
NF, Gain vs. V_{DD}

(V_{CTL}=1.8V, fRF=1575MHz)



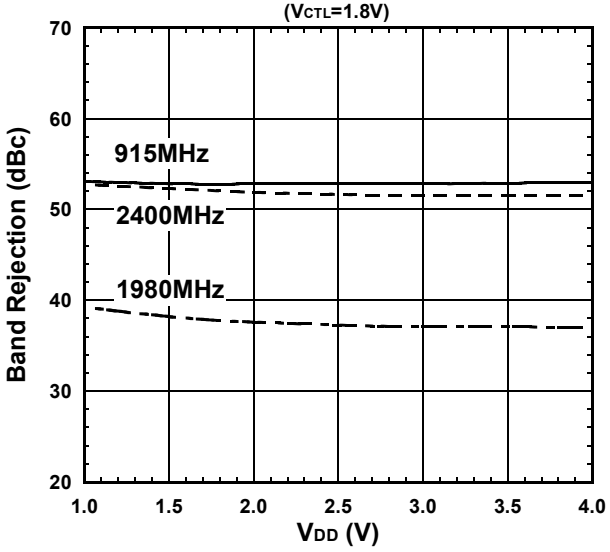
Return Loss vs. V_{DD}

(V_{CTL}=1.8V, fRF=1575MHz)



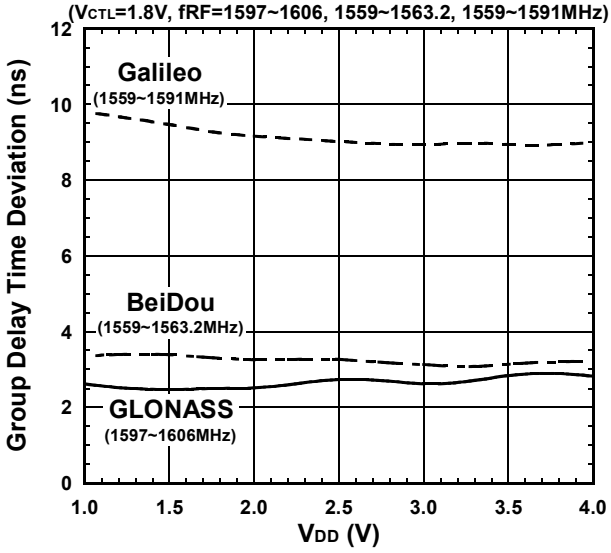
Band Rejection vs. V_{DD}

(V_{CTL}=1.8V)



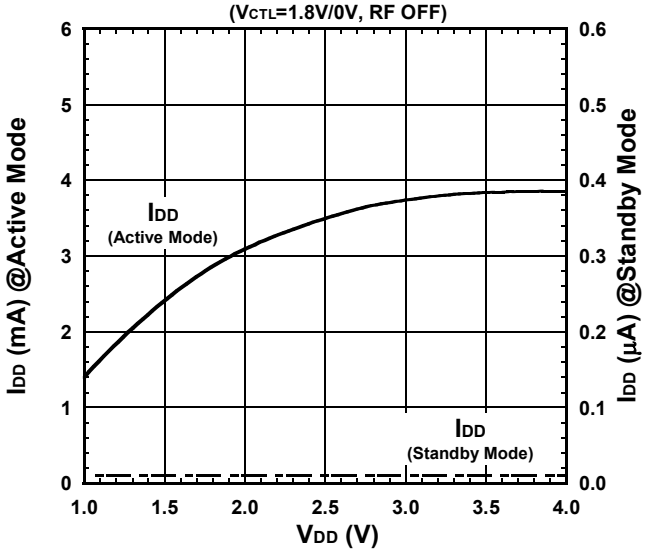
Group Delay Time Deviation vs. V_{DD}

(V_{CTL}=1.8V, fRF=1597~1606, 1559~1563.2, 1559~1591MHz)



I_{DD} vs. V_{DD}

(V_{CTL}=1.8V/0V, RF OFF)

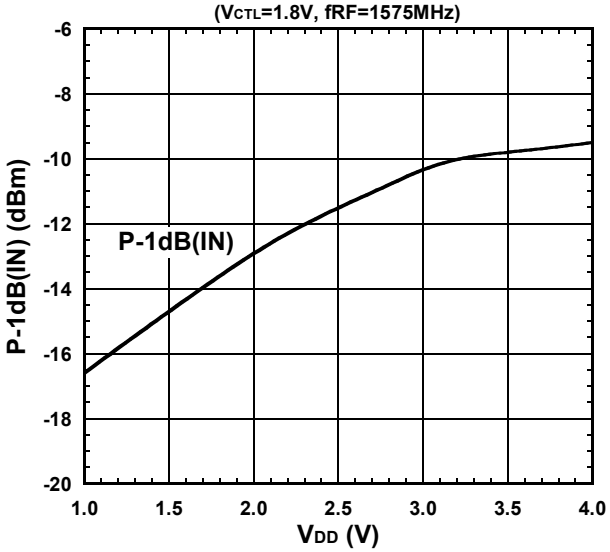


■ ELECTRICAL CHARACTERISTICS

Conditions: V_{CTL}=1.8V, Ta=25°C, Z_s=Z_l=50Ω, with application circuit

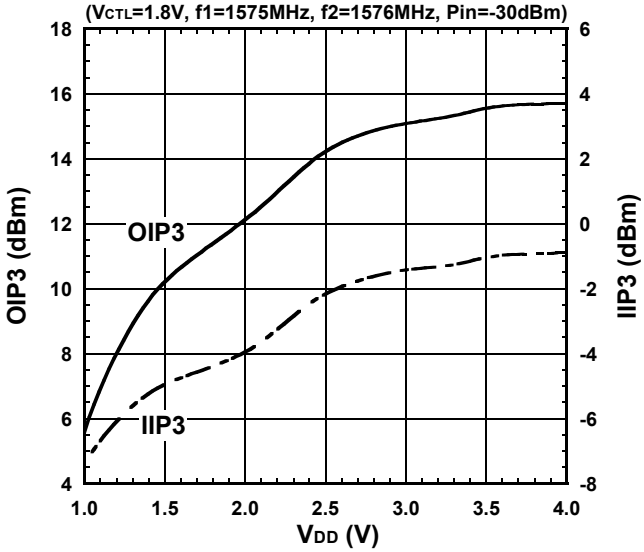
P-1dB(IN) vs. VDD

(VCTL=1.8V, fRF=1575MHz)



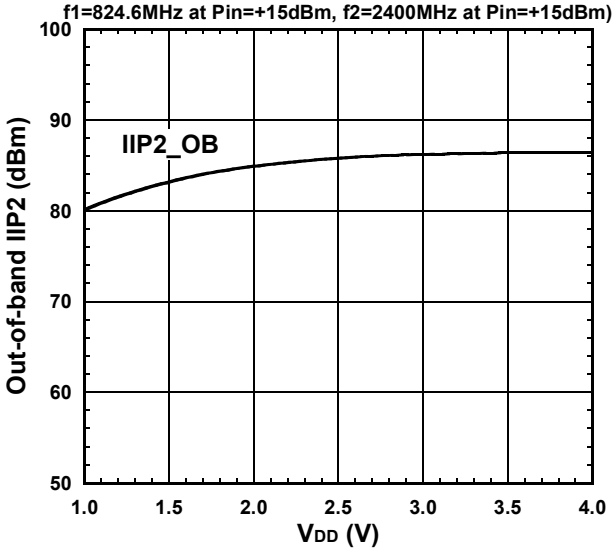
OIP3, IIP3 vs. VDD

(VCTL=1.8V, f1=1575MHz, f2=1576MHz, Pin=-30dBm)



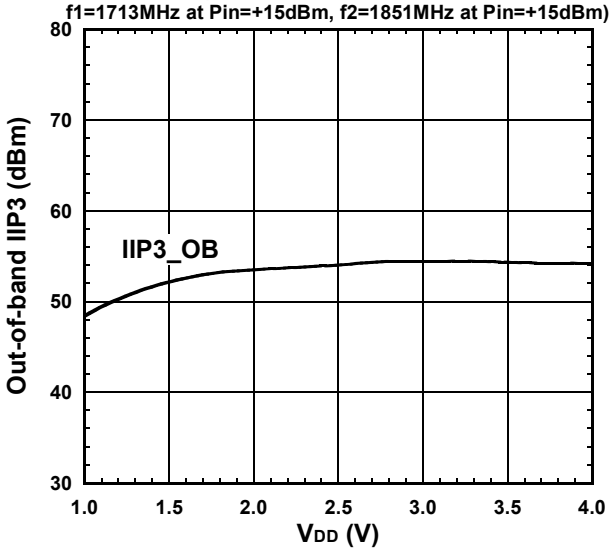
Out-of-band IIP2 vs. VDD

(VCTL=1.8V, fmeas=1575.4MHz,
f1=824.6MHz at Pin=+15dBm, f2=2400MHz at Pin=+15dBm)



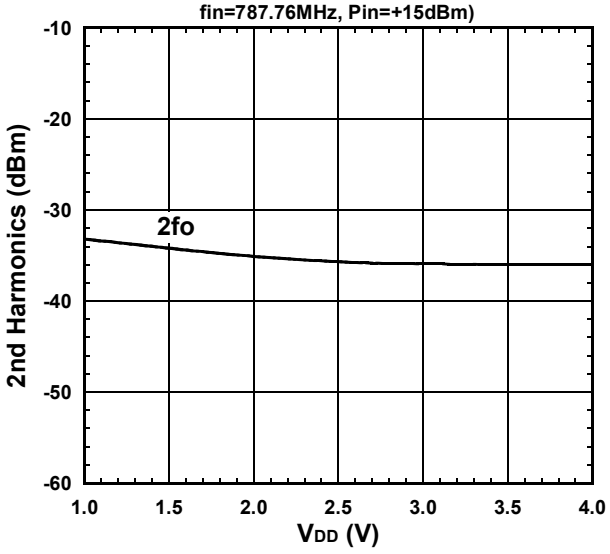
Out-of-band IIP3 vs. VDD

(VCTL=1.8V, fmeas=1575MHz,
f1=1713MHz at Pin=+15dBm, f2=1851MHz at Pin=+15dBm)



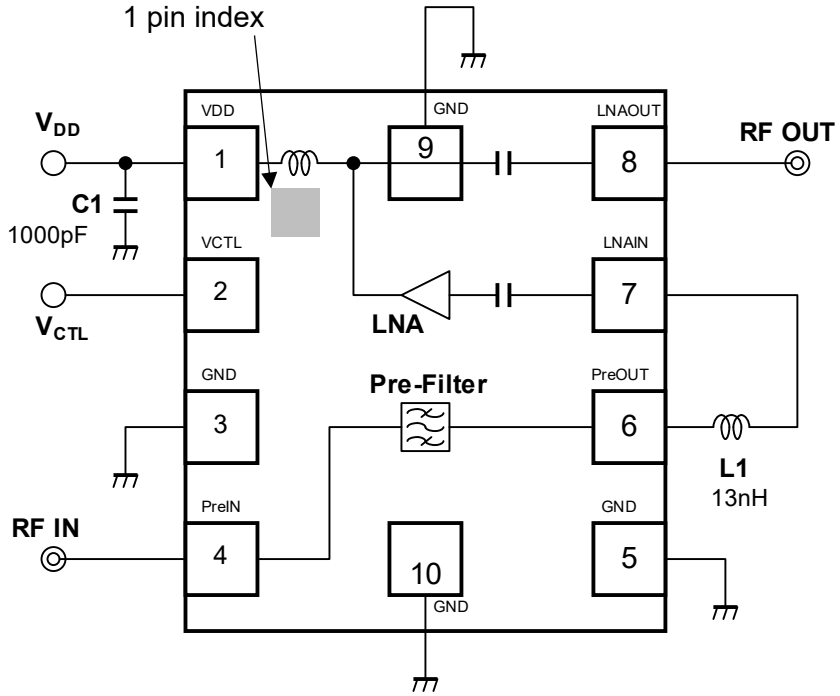
2nd Harmonics vs. VDD

(VCTL=1.8V, fmeas=1575.52MHz,
fin=787.76MHz, Pin=+15dBm)



■ Application circuit

(Top View)

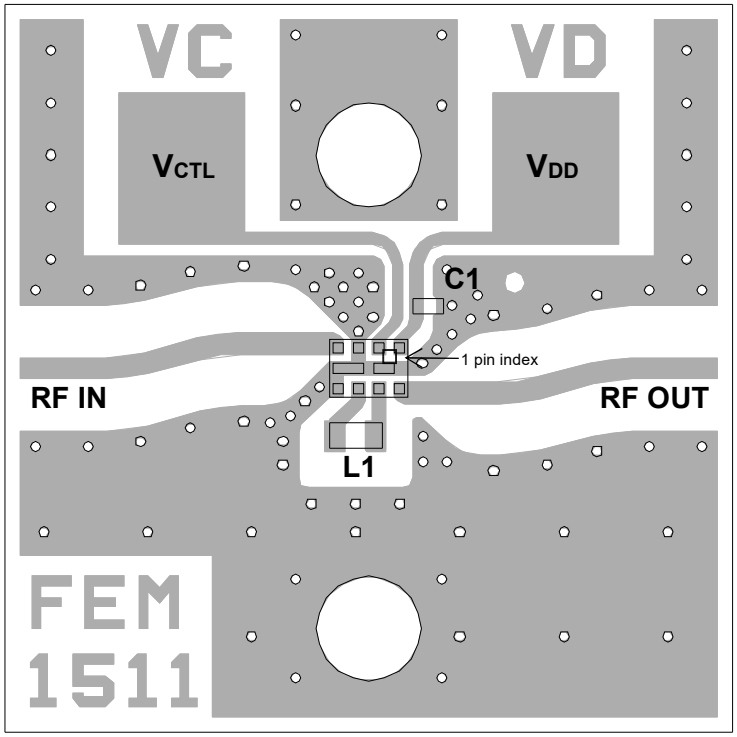


Parts list

Parts ID	Manufacture
L1	LQW15AN_00 Series (MURATA)
C1	GRM03 Series (MURATA)

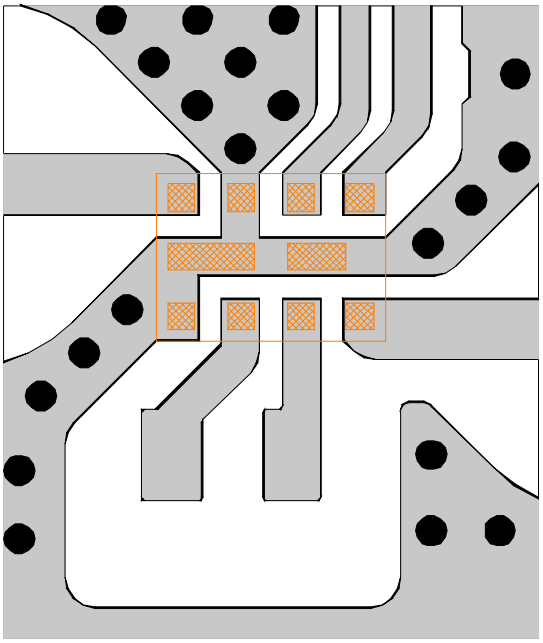
■ Evaluation board

(Top View)



PCB
Substrate: FR-4
Thickness: 0.2mm
Microstrip line width: 0.4mm (Z_0=50Ω)
Size: 14.0mm x 14.0mm

<PCB LAYOUT GUIDELINE>



PCB
PKG Terminal
PKG Outline
GND Via Hole
Diameter ϕ= 0.2mm

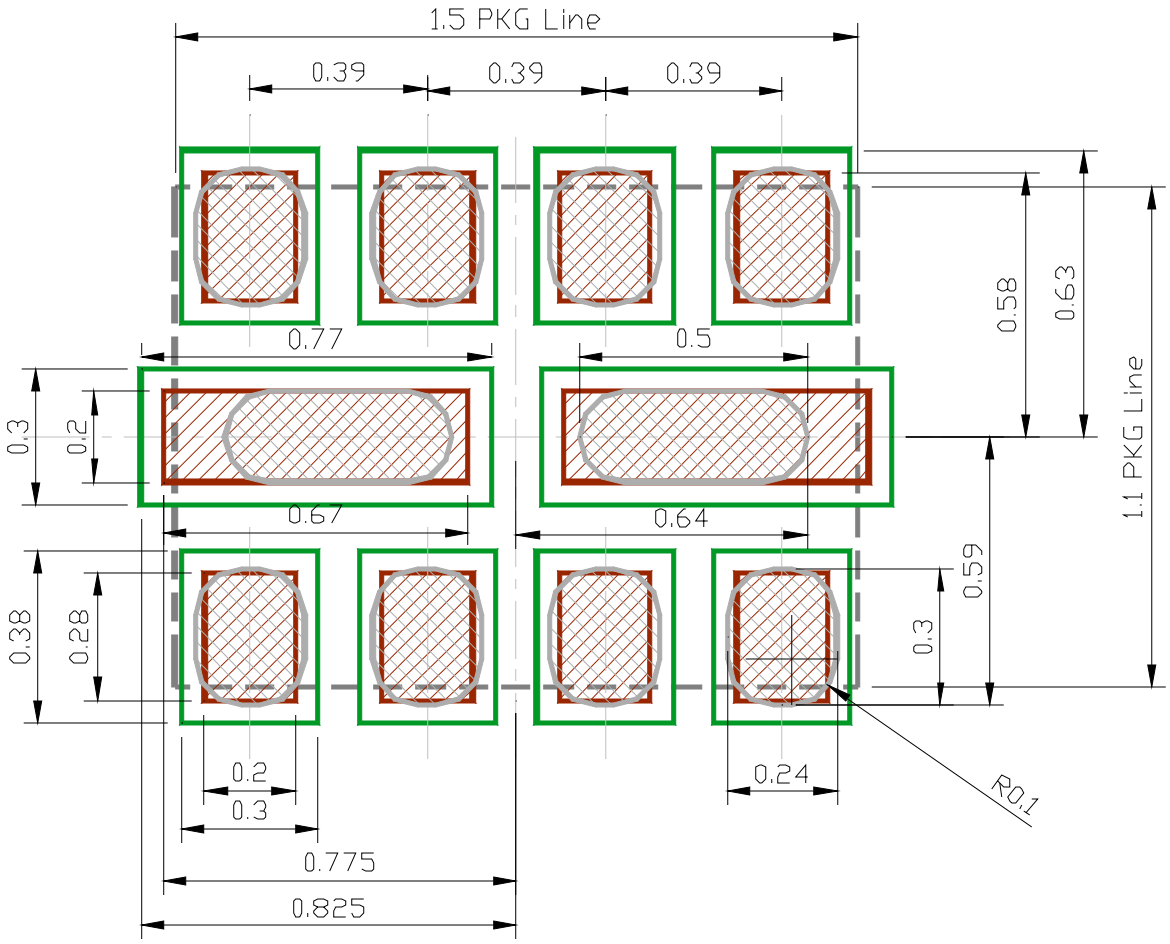
PRECAUTIONS

- Please layout ground pattern under this FEM in order not to couple with RFIN and RFOUT terminal.
- All external parts should be placed as close as possible to the FEM.
- For good RF performance, all GND terminals must be connected to PCB ground plane of substrate, and via-holes for GND should be placed near the FEM.

■ RECOMMENDED FOOTPRINT PATTERN (HFFP10-HH Package) <Reference>

PKG : 1.5mm x 1.1mm
Pin pitch : 0.39mm

: Land
: Mask (Open area) *Metal mask thickness : 100μm
: Resist(Open area)



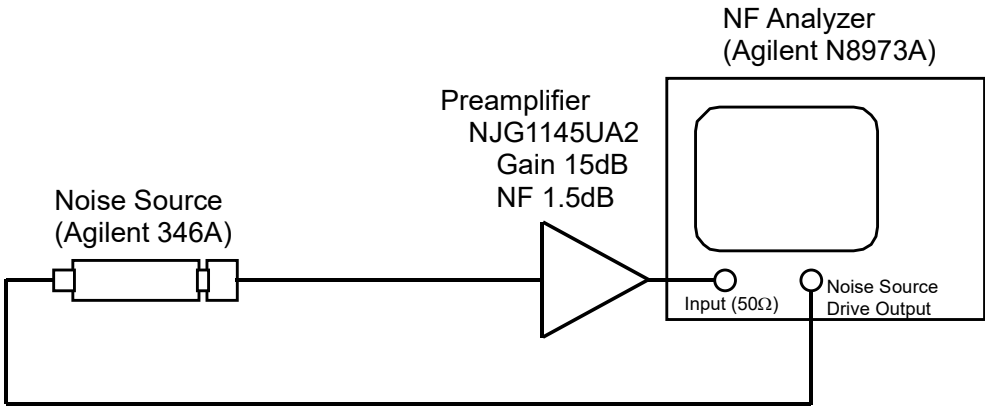
■ NOISE FIGURE MEASUREMENT BLOCK DIAGRAM

Measuring instruments

NF Analyzer : Agilent N8973A
Noise Source : Agilent 346A

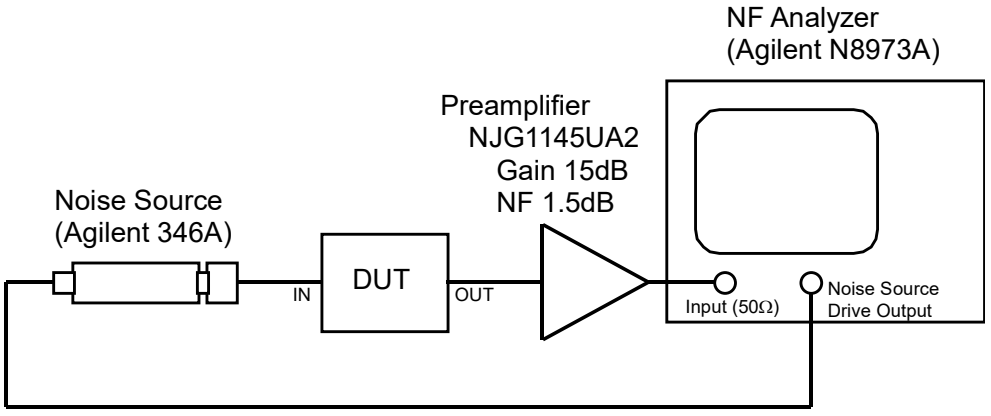
Setting the NF analyzer

Measurement mode form
Device under test : Amplifier
System downconverter : off
Mode setup form
Sideband : LSB
Averages : 16
Average mode : Point
Bandwidth : 4MHz
Loss comp : off
Tcold : setting the temperature of noise source (303.15K)



* Preamplifier is used to improve NF measurement accuracy.
* Noise source, preamplifier and NF analyzer are connected directly.

Calibration setup

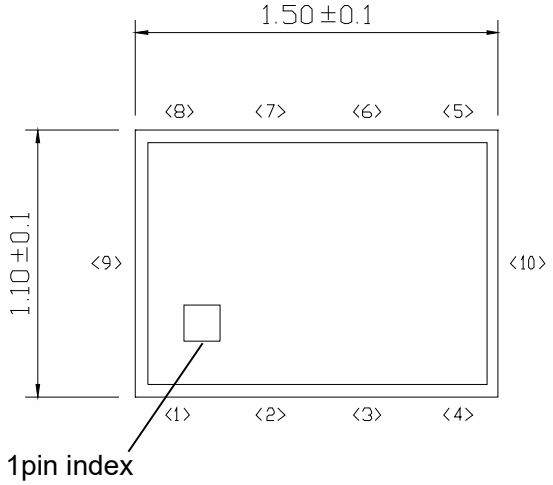


* Noise source, DUT, preamplifier and NF analyzer are connected directly.

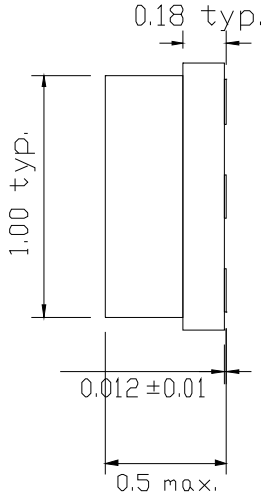
Measurement Setup

■ Package outline (HFFP10-HH)

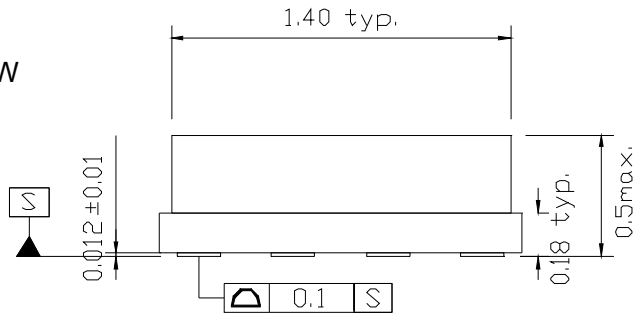
TOP VIEW



SIDE VIEW

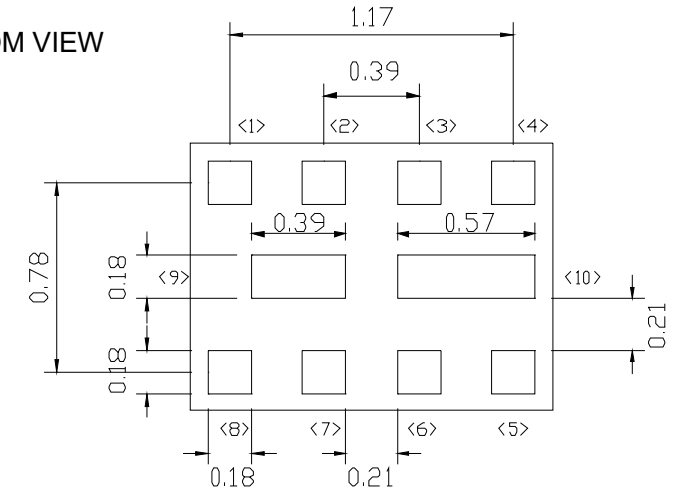


SIDE VIEW



Electrode Dimensions clearance : ±0.05mm

BOTTOM VIEW



Unit	: mm
Substrate	: Ceramic
Terminal treat	: Au
Lid	: SnAg/Kovar/Ni
Weight (typ.)	: 4.6mg

Cautions on using this product

This product contains Gallium-Arsenide (GaAs) which is a harmful material.

- Do NOT eat or put into mouth.
- Do NOT dispose in fire or break up this product.
- Do NOT chemically make gas or powder with this product.
- To waste this product, please obey the relating law of your country.

[CAUTION]
The specifications on this databook are only given for information , without any guarantee as regards either mistakes or omissions.
The application circuits in this databook are described only to show representative usages of the product and not intended for the guarantee or permission of any right including the industrial rights.

This product may be damaged with electric static discharge (ESD) or spike voltage. Please handle with care to avoid these damages.

This product is hollow seal package type, and it is with the structure susceptible to stress from the outside. Therefore, note the following in relation to the contents, after conducting an evaluation, please use.
1. After mounting this product, to implement the potting and transfer molding, please the confirmation of resistance to temperature changes and shrinkage stress involved in the molding.
2. When mounted on the product, collet diameter please use more than 1mmφ. In addition, the value of static load is recommended mounting less than 5N.
3. For dynamic load at the time of mounting, please use it after confirming in consideration of the contact area / speed / load.

1. The products and the product specifications described in this document are subject to change or discontinuation of production without notice for reasons such as improvement. Therefore, before deciding to use the products, please refer to our sales representatives for the latest information thereon.
2. The materials in this document may not be copied or otherwise reproduced in whole or in part without the prior written consent of us.
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5. The products listed in this document are intended and designed for use as general electronic components in standard applications (office equipment, telecommunication equipment, measuring instruments, consumer electronic products, amusement equipment etc.). Those customers intending to use a product in an application requiring extreme quality and reliability, for example, in a highly specific application where the failure or misoperation of the product could result in human injury or death should first contact us.
    - Aerospace Equipment
    - Equipment Used in the Deep Sea
    - Power Generator Control Equipment (nuclear, steam, hydraulic, etc.)
    - Life Maintenance Medical Equipment
    - Fire Alarms / Intruder Detectors
    - Vehicle Control Equipment (automotive, airplane, railroad, ship, etc.)
    - Various Safety Devices
    - Traffic control system
    - Combustion equipment

    In case your company desires to use this product for any applications other than general electronic equipment mentioned above, make sure to contact our company in advance. Note that the important requirements mentioned in this section are not applicable to cases where operation requirements such as application conditions are confirmed by our company in writing after consultation with your company.
6. We are making our continuous effort to improve the quality and reliability of our products, but electronic device products are likely to fail with certain probability. In order to prevent any injury to persons or damages to property resulting from such failure, customers should be careful enough to incorporate safety measures in their design, such as redundancy feature, fire containment feature and fail-safe feature. We do not assume any liability or responsibility for any loss or damage arising from misuse or inappropriate use of the products.
7. The products have been designed and tested to function within controlled environmental conditions. Do not use products under conditions that deviate from methods or applications specified in this datasheet. Failure to employ the products in the proper applications can lead to deterioration, destruction or failure of the products. We shall not be responsible for any bodily injury, fires or accident, property damage or any consequential damages resulting from misuse or misapplication of the products.
8. Quality Warranty
    8-1. Quality Warranty Period
    In the case of a product purchased through an authorized distributor or directly from us, the warranty period for this product shall be one (1) year after delivery to your company. For defective products that occurred during this period, we will take the quality warranty measures described in section 8-2. However, if there is an agreement on the warranty period in the basic transaction agreement, quality assurance agreement, delivery specifications, etc., it shall be followed.
    8-2. Quality Warranty Remedies
    When it has been proved defective due to manufacturing factors as a result of defect analysis by us, we will either deliver a substitute for the defective product or refund the purchase price of the defective product.
    Note that such delivery or refund is sole and exclusive remedies to your company for the defective product.
    8-3. Remedies after Quality Warranty Period
    With respect to any defect of this product found after the quality warranty period, the defect will be analyzed by us. On the basis of the defect analysis results, the scope and amounts of damage shall be determined by mutual agreement of both parties. Then we will deal with upper limit in Section 8-2. This provision is not intended to limit any legal rights of your company.
9. Anti-radiation design is not implemented in the products described in this document.
10. The X-ray exposure can influence functions and characteristics of the products. Confirm the product functions and characteristics in the evaluation stage.
11. Warning for handling Gallium and Arsenic (GaAs) products (Applying to GaAs MMIC, Photo Reflector). These products use Gallium (Ga) and Arsenic (As) which are specified as poisonous chemicals by law. For the prevention of a hazard, do not burn, destroy, or process chemically to make them as gas or power. When the product is disposed of, please follow the related regulation and do not mix this with general industrial waste or household waste.
12. Front end module product is hollow seal package type, and it is with the structure susceptible to stress from the outside. Therefore, note the following in relation to the contents, after conducting an evaluation. please use.
    12-1. After mounting this product, to implement the potting and transfer molding, please the confirmation of resistance to temperature changes and shrinkage stress involved in the molding.
    12-2. When mounted on the product, collet diameter please use more than 1mmφ. In addition, the value of static load is recommended mounting less than 5N.
    12-3. For dynamic load at the time of mounting. please use it after confirming in consideration of the contact area /speed /load.
13. Please contact our sales representatives should you have any questions or comments concerning the products or the technical information.